



PFC Device Corporation

## PRM011N10D

### 100V Single N-Channel MOSFET

#### Major ratings and characteristics

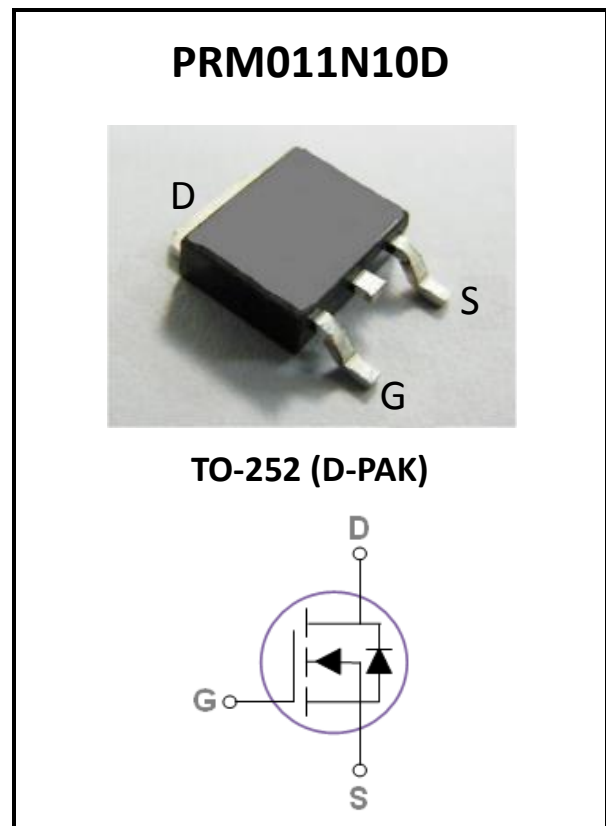
Characteristics	Values	Units
$V_{DS}$	100	V
$I_D^5$ ( $T_C=25^\circ\text{C}$ )	66	A
Max. $R_{DS(ON)}$ @ $V_{GS}=10\text{V}$	11	m $\Omega$
Max. $R_{DS(ON)}$ @ $V_{GS}=4.5\text{V}$	15	m $\Omega$
$T_J$ Operating Junction Temperature	-55 to +150	$^\circ\text{C}$

#### General Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.

#### Typical Applications

- Charger Adapter
- Power Tools
- LED Lighting



#### Features

- Max.  $R_{DS(ON)}=11\text{m}\Omega$ @ $V_{GS}=10\text{V}$
- Improved dv/dt capability
- Fast switching
- 100%  $E_{AS}$  Guaranteed
- Green Device Available

## 1. Characteristics

### Maximum Ratings Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise specified )

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D^5$	Drain Current – Continuous ( $T_C=25^\circ\text{C}$ )	66	A
	Drain Current – Continuous ( $T_C=100^\circ\text{C}$ )	42	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	265	A
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	26	mJ
$I_{AS}$	Single Pulse Avalanche Current <sup>2</sup>	23	A
$P_D$	Power Dissipation ( $T_C=25^\circ\text{C}$ )	83	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.6	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62.5	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.5	$^\circ\text{C/W}$



## Electrical Characteristics ( T<sub>J</sub> = 25 °C unless otherwise specified )

### Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

### On Characteristics

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	9.3	11	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	12	15	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.6	2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =10A	---	36	---	S

### Dynamic and switching Characteristics

Q <sub>g</sub>	Total Gate Charge <sup>3, 4</sup>	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	25	---	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3, 4</sup>		---	4	---	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3, 4</sup>		---	6	---	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3, 4</sup>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =20A	---	8	---	ns
T <sub>r</sub>	Turn-On Rise Time <sup>3, 4</sup>		---	40	---	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3, 4</sup>		---	24	---	
T <sub>f</sub>	Turn-Off Fall Time <sup>3, 4</sup>		---	75	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	---	1470	---	pF
C <sub>oss</sub>	Output Capacitance		---	256	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	23	---	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	---	0.7	---	Ω

### Drain-Source Diode Characteristics

V <sub>SD</sub>	Source to Drain Diode Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	---	---	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =20A, di/dt=100A/us	---	29	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge		---	21	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, L=0.1mH, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C
3. The data tested by pulsed , pulse width ≤300us , duty cycle ≤2%.
4. Essentially independent of operating temperature.
5. Silicon limited.



2. Characteristics Curves

Ratings and Characteristics Curves

(  $T_A = 25^{\circ}\text{C}$  unless otherwise specified )

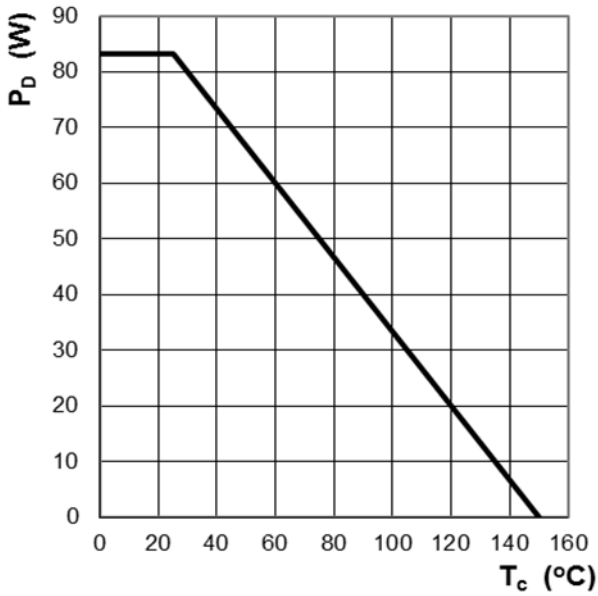


Figure 1: Power Dissipation

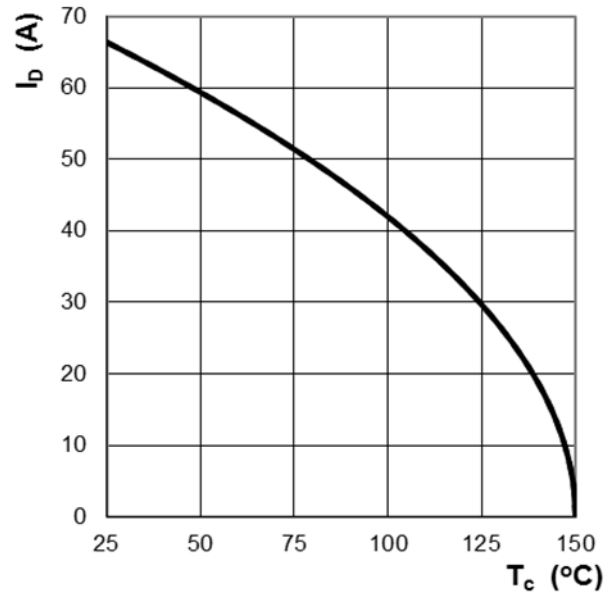


Figure 2: Continuous Drain Current vs.  $T_c$

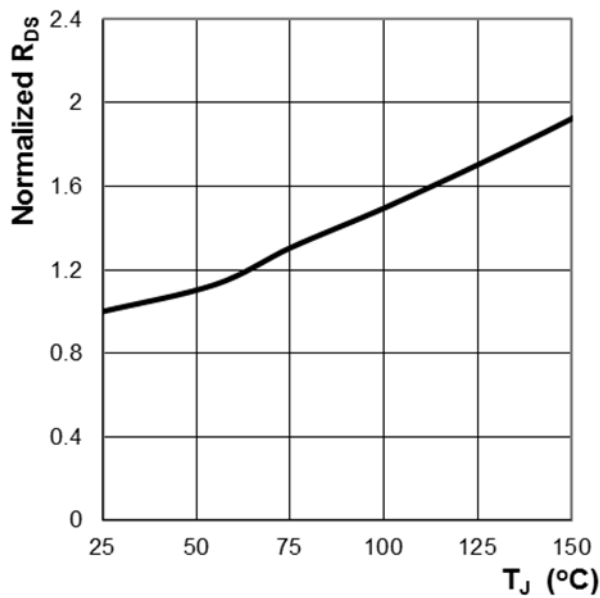


Figure 3: Normalized  $R_{DS(on)}$  vs.  $T_j$

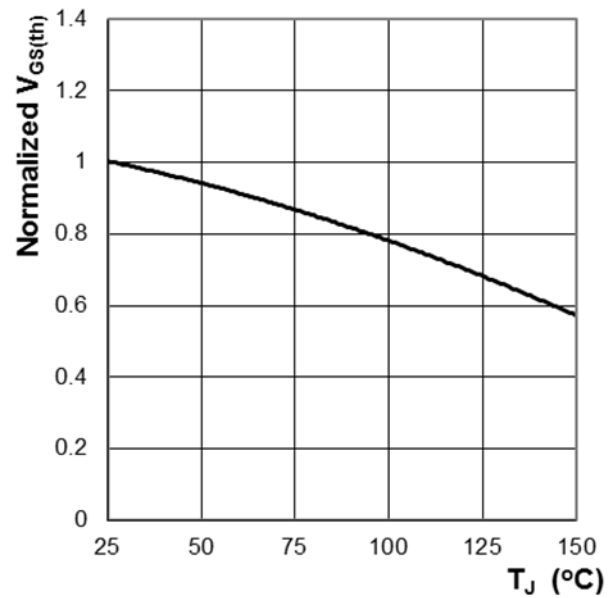


Figure 4: Normalized  $V_{th}$  vs.  $T_j$



## Ratings and Characteristics Curves

(  $T_A = 25^\circ\text{C}$  unless otherwise specified )

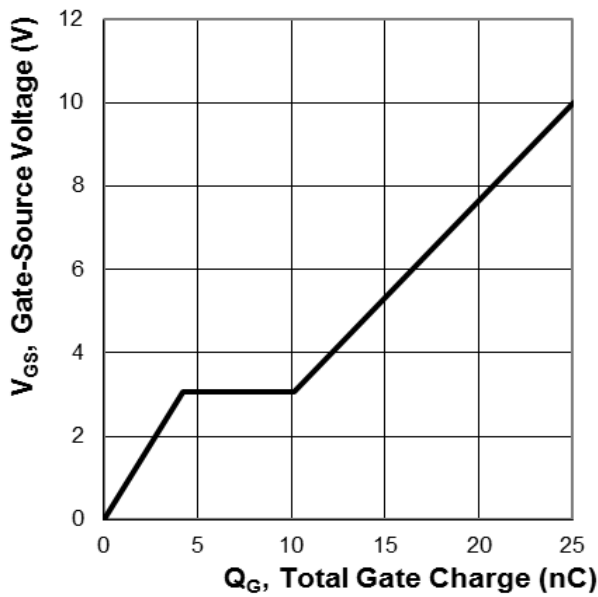


Figure 5: Typ. Gate Charge Characteristics

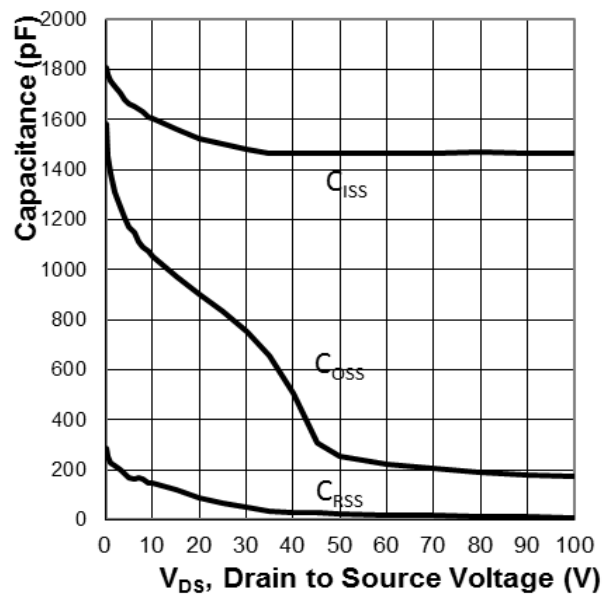


Figure 6: Typ. Capacitance Characteristics

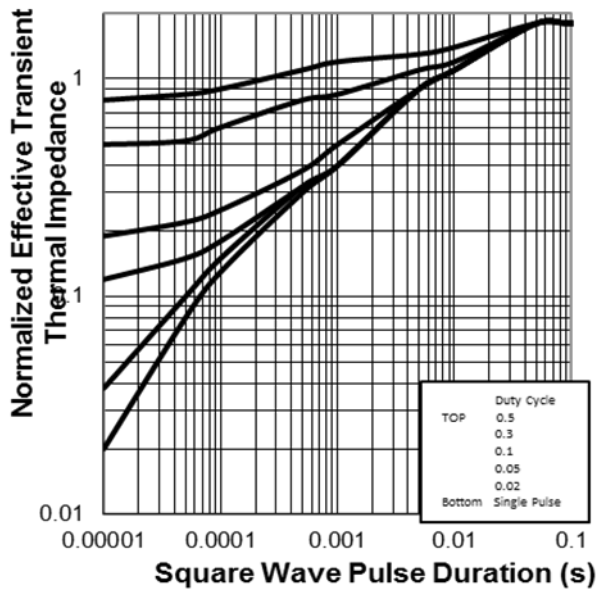


Figure 7: Normalized Thermal Transient Impedance, Junction-to-Case

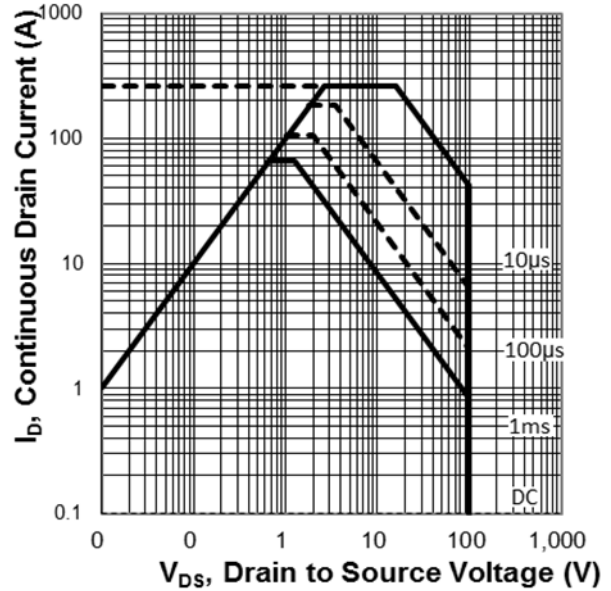
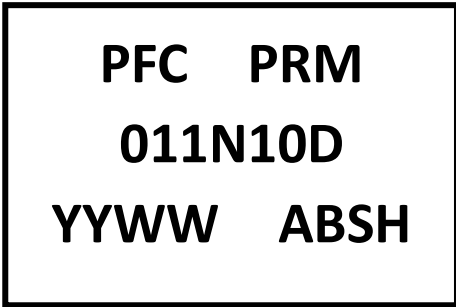


Figure 8: Maximum Safe Operation Area



3. Marking information

Top Marking Rule



PRM011N10D = Product Type Marking Code

YYWW = Date Code

YY = Last two digits of year

WW = Week code

ABS = Assembly code

H = Halogen Free (N/A = common molding compound)

4. Package information

Package Outline Dimensions millimeters

**TO-252 ( DPAK )**

Dim.	Min.	Max.
A	6.30	6.90
B	5.10	5.60
C	3.50	-----
D	4.60	-----
E	9.40	10.60
F	0.50	1.20
G	0.70	0.90
H	0.50	0.90
I	0.50	0.90
J	2.30 Ref.	
K	5.40	6.30
L	2.40	3.40
M	2.10	2.50
N	0.35	0.65
O	-----	0.20
P	1.40	1.90

All Dimensions in millimeter



**5. Ordering information**

Part Number	Package	Delivery mode
PRM011N10D	TO-252 (D-PAK)	2500 pcs / 13" diameter reel

Mechanical

- Molder Plastic: UL Flammability Classification Rating 94V-0
- Device Weight : 0.01 ounces (0.3grams) - TO-252 (D-PAK)

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